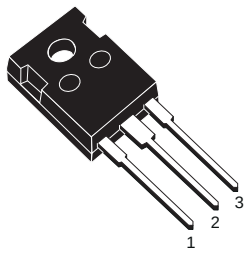
STW8NB90
STH8NB90FI

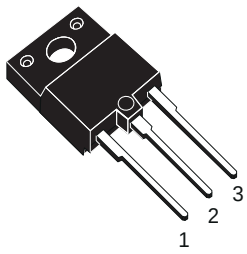
N-CHANNEL 900V - 1.1 Ω - 8 A TO-247/ISOWATT218
PowerMesh™ MOSFET

TYPE	V_{DSS}	$R_{DS(on)}$	I_D
STW8NB90	900 V	< 1.45 Ω	8 A
STH8NB90FI	900 V	< 1.45 Ω	5 A

- TYPICAL R_{DS}(on) = 1.1 Ω
- EXTREMELY HIGH dv/dt CAPABILITY
- 100% AVALANCHE TESTED
- VERY LOW INTRINSIC CAPACITANCES
- GATE CHARGE MINIMIZED



TO-247



ISOWATT218

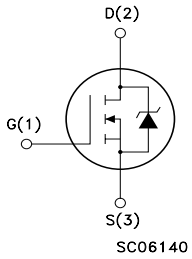
DESCRIPTION

Using the latest high voltage MESH OVERLAY™ process, STMicroelectronics has designed an advanced family of power MOSFETs with outstanding performances. The new patent pending strip layout coupled with the Company's proprieraty edge termination structure, gives the lowest $R_{DS(on)}$ per area, exceptional avalanche and dv/dt capabilities and unrivalled gate charge and switching characteristics.

APPLICATIONS

- HIGH CURRENT, HIGH SPEED SWITCHING
- SWITH MODE POWER SUPPLIES (SMPS)
- DC-AC CONVERTERS FOR WELDING EQUIPMENT

INTERNAL SCHEMATIC DIAGRAM



ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Value		Unit
		STW8NB90	STH8NB90FI	
V_{DS}	Drain-source Voltage (V_{GS} = 0)	900		V
V_{DGR}	Drain-gate Voltage (R_{GS} = 20 kΩ)	900		V
V_{GS}	Gate- source Voltage	±30		V
I_D	Drain Current (continuos) at T_C = 25°C	8	5	A
I_D	Drain Current (continuos) at T_C = 100°C	5	3	A
I_{DM} (•)	Drain Current (pulsed)	32	20	A
P_{TOT}	Total Dissipation at T_C = 25°C	200	80	W
	Derating Factor	1.6	0.64	W/°C
dv/dt (1)	Peak Diode Recovery voltage slope	4		V/ns
V_{ISO}	Insulation Withstand Voltage (DC)	-	2500	V
T_{stg}	Storage Temperature	–65 to 150		°C
T_j	Max. Operating Junction Temperature	150		°C

(•)Pulse width limited by safe operating area

(1)I_{SD} ≤8 A, di/dt ≤200A/µs, $V_{DD} \leq V_{(BR)DSS}$, $T_j \leq T_{JMAX}$.

THERMAL DATA

		TO-247	ISOWATT218	
Rthj-case	Thermal Resistance Junction-case Max	0.625	1.56	°C/W
Rthj-amb	Thermal Resistance Junction-ambient Max	30		°C/W
T_l	Maximum Lead Temperature For Soldering Purpose	300		°C

AVALANCHE CHARACTERISTICS

Symbol	Parameter	Max Value	Unit
I_{AR}	Avalanche Current, Repetitive or Not-Repetitive (pulse width limited by T_j max)	8	A
E_{AS}	Single Pulse Avalanche Energy (starting T_j = 25 °C, $I_D = I_{AR}$, V_{DD} = 50 V)	700	mJ

ELECTRICAL CHARACTERISTICS (TCASE = 25 °C UNLESS OTHERWISE SPECIFIED)

OFF

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$V_{(BR)DSS}$	Drain-source Breakdown Voltage	I_D = 250 µA, V_{GS} = 0	900			V
I_{DSS}	Zero Gate Voltage Drain Current (V_{GS} = 0)	V_{DS} = Max Rating			1	µA
		V_{DS} = Max Rating, T_C = 125 °C			50	µA
I_{GSS}	Gate-body Leakage Current (V_{DS} = 0)	V_{GS} = ±30V			±100	nA

ON (1)

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS} = V_{GS}$, I_D = 250 µA	3	4	5	V
$R_{DS(on)}$	Static Drain-source On Resistance	V_{GS} = 10 V, I_D = 4 A		1.1	1.45	Ω

DYNAMIC

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
g_{fs} (1)	Forward Transconductance	$V_{DS} > I_{D(on)} \times R_{DS(on)max}$, I_D = 4 A		8		S
C_{iss}	Input Capacitance	V_{DS} = 25V, f = 1 MHz, V_{GS} = 0		2120		pF
C_{oss}	Output Capacitance			225		pF
C_{rss}	Reverse Transfer Capacitance			23		pF

ELECTRICAL CHARACTERISTICS (CONTINUED)

SWITCHING ON

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$t_{d(on)}$	Turn-on Delay Time	V_{DD} = 450 V, I_D = 3.5 A		25		ns
t_r	Rise Time	R_G = 4.7Ω V_{GS} = 10 V (see test circuit, Figure 3)		12		ns
Q_g	Total Gate Charge	V_{DD} = 400V, I_D = 9A,		46	72	nC
Q_{gs}	Gate-Source Charge	V_{GS} = 10V		12.5		nC
Q_{gd}	Gate-Drain Charge			18		nC

SWITCHING OFF

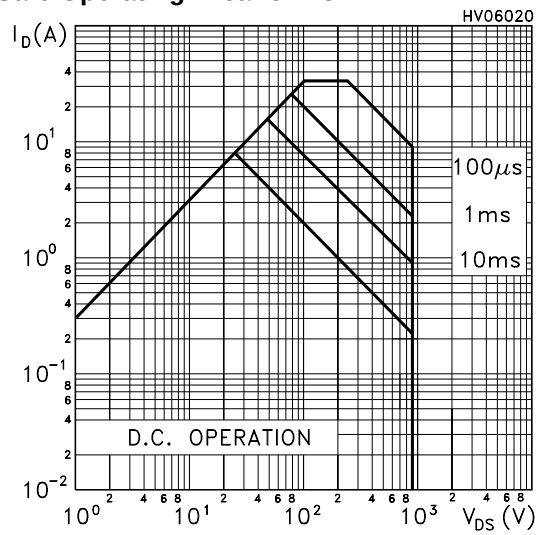
Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$t_{r(Voff)}$	Off-voltage Rise Time	V_{DD} = 720V, I_D = 7.4 A,		22		ns
t_f	Fall Time	R_G = 4.7Ω, V_{GS} = 10V (see test circuit, Figure 5)		15		ns
t_c	Cross-over Time			31		ns

SOURCE DRAIN DIODE

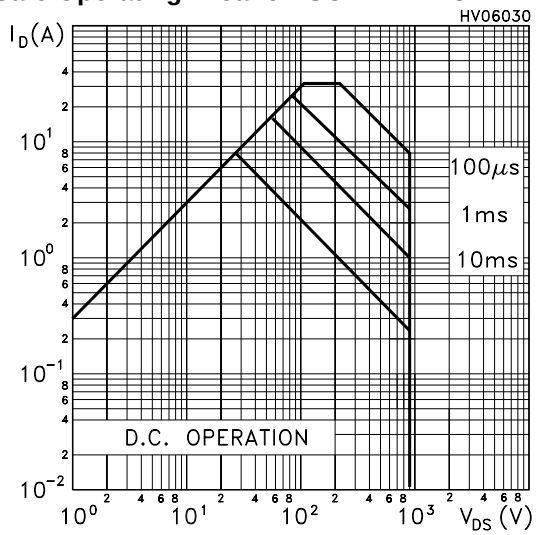
Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
I_{SD}	Source-drain Current				8	A
I_{SDM} (2)	Source-drain Current (pulsed)				32	A
V_{SD} (1)	Forward On Voltage	I_{SD} = 8 A, V_{GS} = 0			1.6	V
t_{rr}	Reverse Recovery Time	I_{SD} = 7.4 A, di/dt = 100A/µs,		700		ns
Q_{rr}	Reverse Recovery Charge	V_{DD} = 100V, T_j = 150°C (see test circuit, Figure 5)		6.3		µC
I_{RRM}	Reverse Recovery Current			18		A

Note: 1. Pulsed: Pulse duration = 300 µs, duty cycle 1.5 %.
2. Pulse width limited by safe operating area.

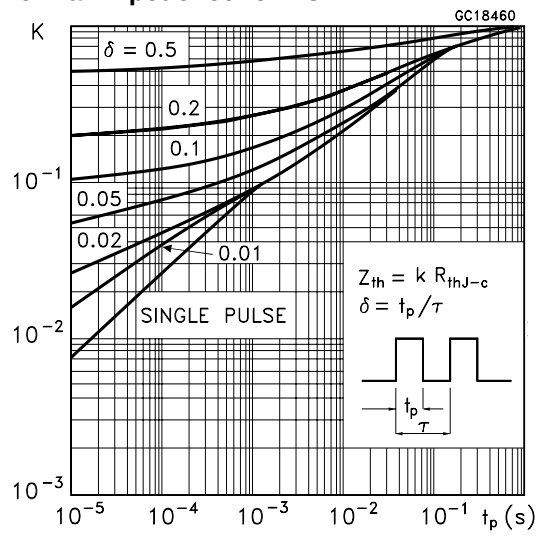
Safe Operating Area for TO-247



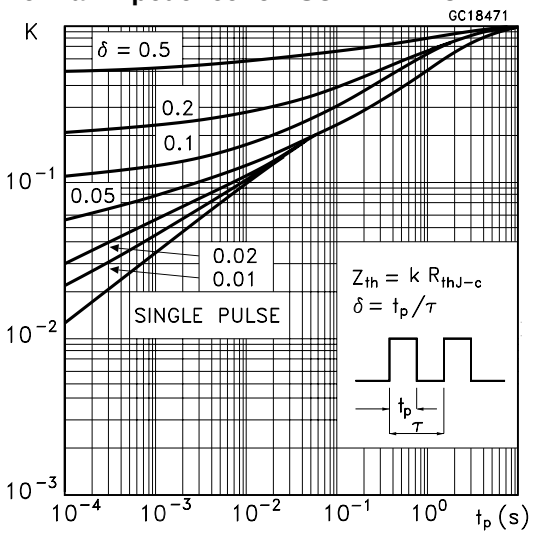
Safe Operating Area for ISOWATT218



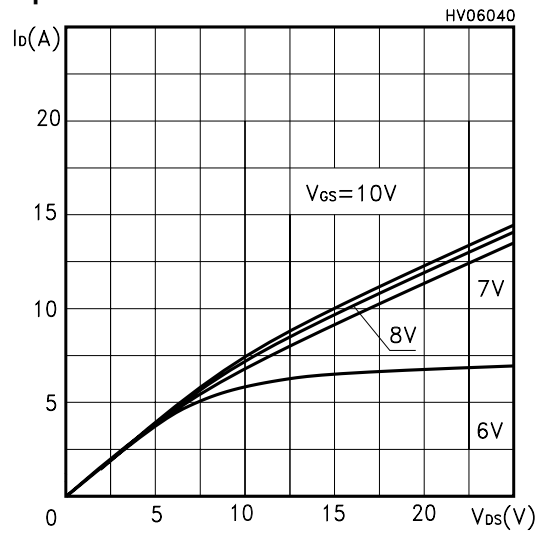
Thermal Impedence for TO-247



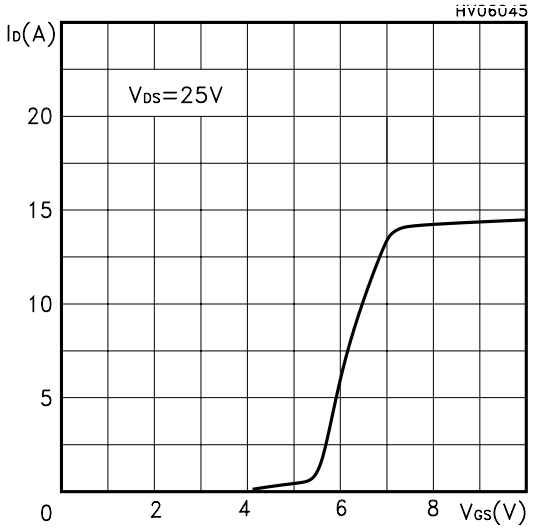
Thermal Impedence for ISOWATT218



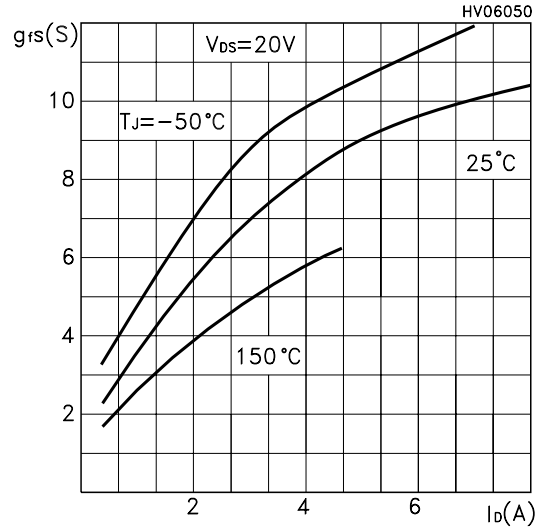
Output Characteristics



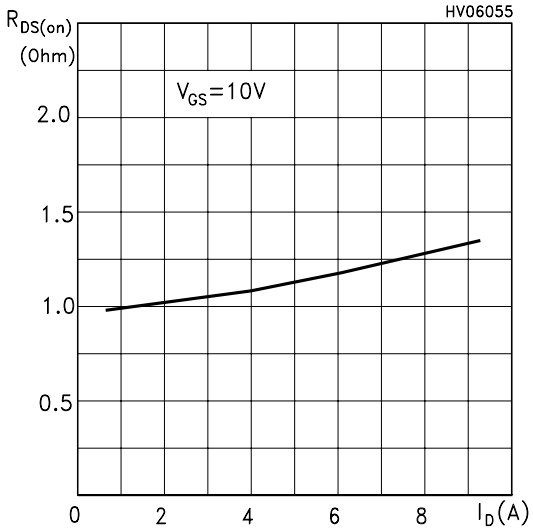
Transfer Characteristics



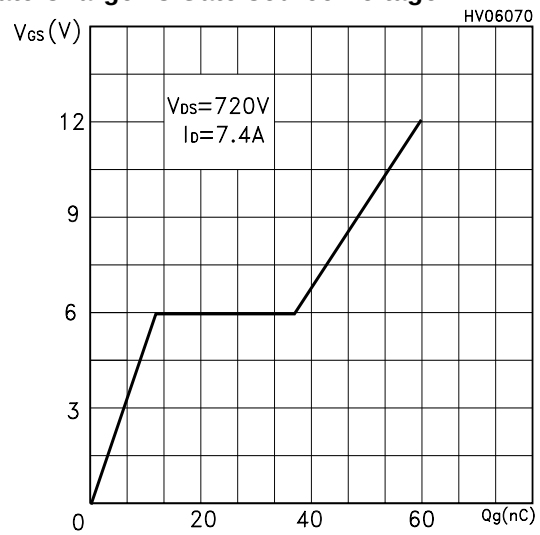
Transconductance



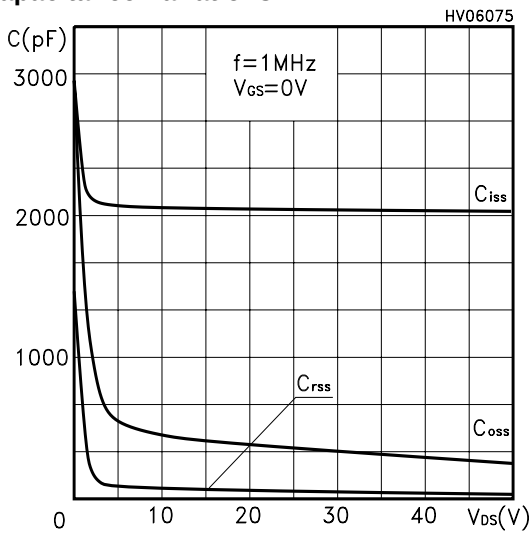
Static Drain-source On Resistance



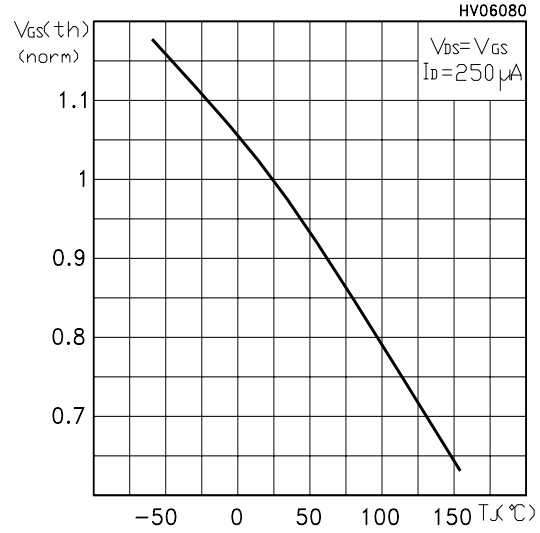
Gate Charge vs Gate-source Voltage



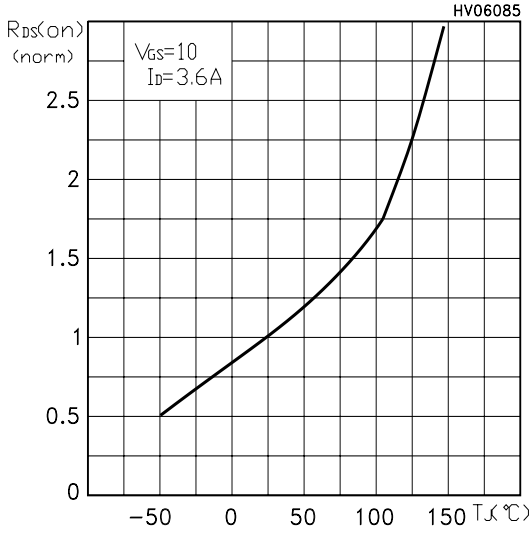
Capacitance Variations



Normalized Gate Thereshold Voltage vs Temp.



Normalized On Resistance vs Temperature



Source-drain Diode Forward Characteristics

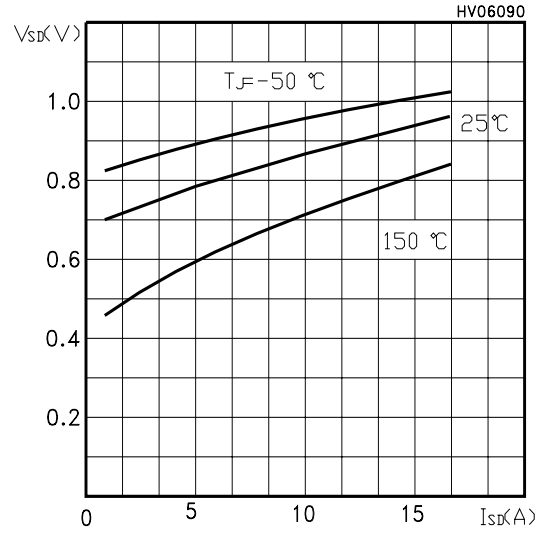


Fig. 1: Unclamped Inductive Load Test Circuit

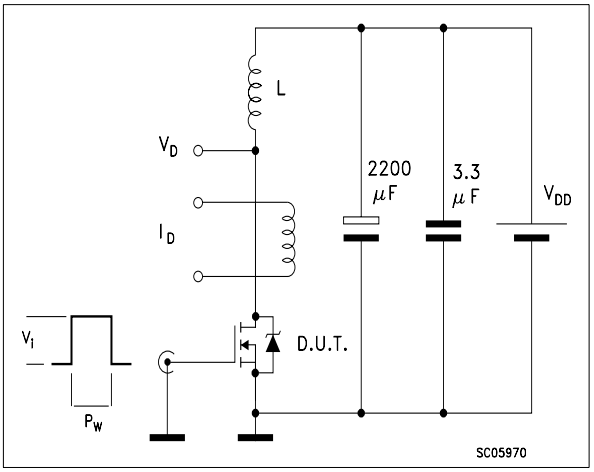


Fig. 2: Unclamped Inductive Waveform

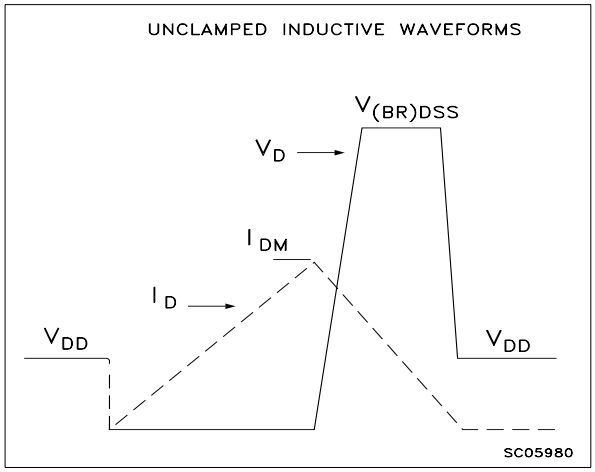


Fig. 3: Switching Times Test Circuit For Resistive Load

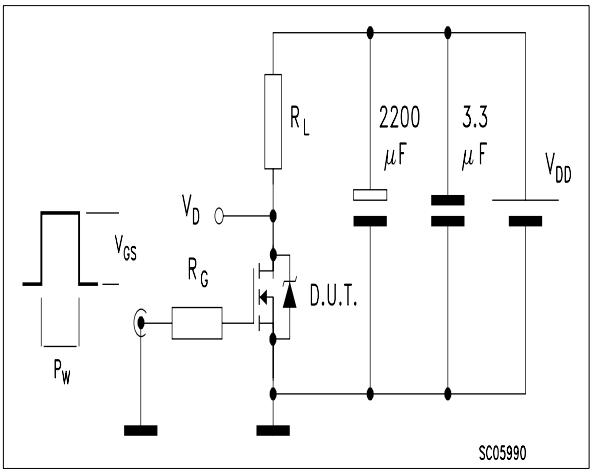


Fig. 4: Gate Charge test Circuit

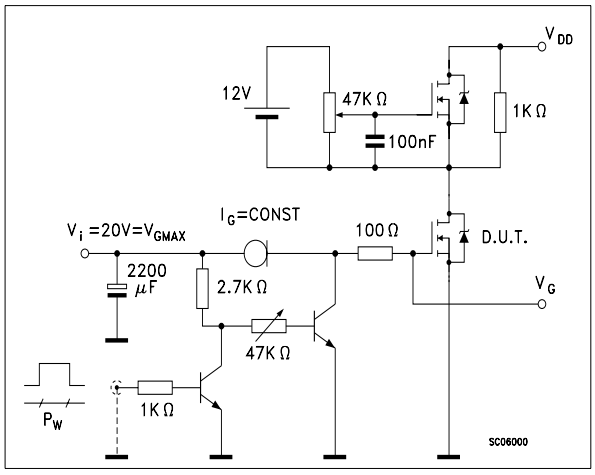
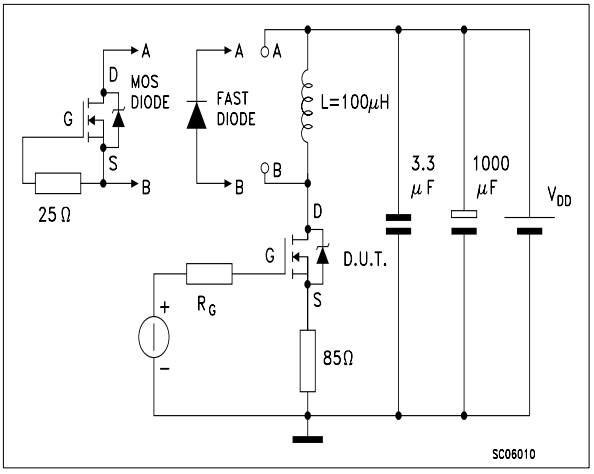
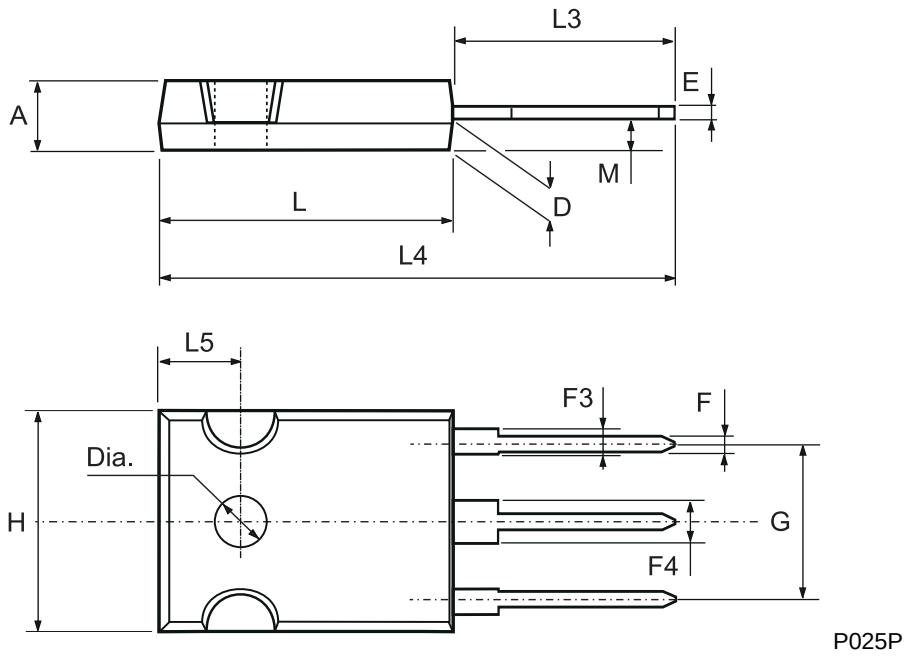


Fig. 5: Test Circuit For Inductive Load Switching And Diode Recovery Times



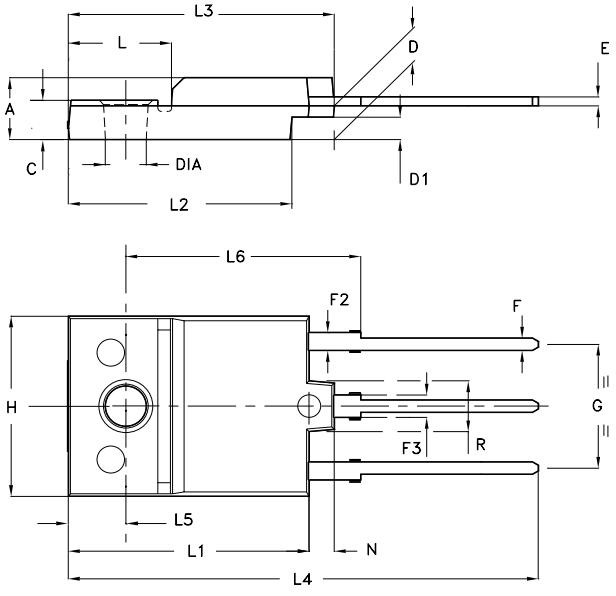
TO-247 MECHANICAL DATA

DIM.	mm			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
A	4.7		5.3	0.185		0.209
D	2.2		2.6	0.087		0.102
E	0.4		0.8	0.016		0.031
F	1		1.4	0.039		0.055
F3	2		2.4	0.079		0.094
F4	3		3.4	0.118		0.134
G		10.9			0.429	
H	15.3		15.9	0.602		0.626
L	19.7		20.3	0.776		0.779
L3	14.2		14.8	0.559		0.582
L4		34.6			1.362	
L5		5.5			0.217	
M	2		3	0.079		0.118



ISOWATT218 MECHANICAL DATA

DIM.	mm			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
A	5.35		5.65	0.211		0.222
C	3.30		3.80	0.130		0.150
D	2.90		3.10	0.114		0.122
D1	1.88		2.08	0.074		0.082
E	0.75		0.95	0.030		0.037
F	1.05		1.25	0.041		0.049
F2	1.50		1.70	0.059		0.067
F3	1.90		2.10	0.075		0.083
G	10.80		11.20	0.425		0.441
H	15.80		16.20	0.622		0.638
L		9			0.354	
L1	20.80		21.20	0.819		0.835
L2	19.10		19.90	0.752		0.783
L3	22.80		23.60	0.898		0.929
L4	40.50		42.50	1.594		1.673
L5	4.85		5.25	0.191		0.207
L6	20.25		20.75	0.797		0.817
N	2.1		2.3	0.083		0.091
R		4.6			0.181	
DIA	3.5		3.7	0.138		0.146



- Weight : 4.9 g (typ.)
- Maximum Torque (applied to mounting flange) Recommended: 0.8 Nm; Maximum: 1 Nm
- The side of the dissipator must be flat within 80 µm

P025C/A